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(54) **SEMICONDUCTOR DEVICE HAVING CUT GATE DIELECTRIC**

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(57)

**ABSTRACT**

A device includes a semiconductor fin, a gate structure, gate spacers, and a dielectric feature. The semiconductor fin is over a substrate. The gate structure is over the semiconductor fin and includes a gate dielectric layer over the semiconductor fin and a gate metal covering the gate dielectric layer. The gate spacers are on opposite sides of the gate structure. The dielectric feature is over the substrate. The dielectric feature is in contact with the gate metal, the gate dielectric layer, and the gate spacers, and an interface between the gate metal and the dielectric feature is substantially aligned with an interface between the dielectric feature and one of the gate spacers.

